

High Speed Infrared Emitting Diode, 850 nm, Surface Emitter Technology



22114

DESCRIPTION

VSLY5850 is an infrared, 850 nm emitting diode based on GaAlAs surface emitter chip technology with extreme high radiant intensity, high optical power and high speed, molded in a clear, untinted plastic package, with a parabolic lens.

FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): \varnothing 5
- Leads with stand-off
- Peak wavelength: $\lambda_p = 850$ nm
- High reliability
- High radiant power
- High radiant intensity
- Narrow angle of half intensity: $\varphi = \pm 3^\circ$
- Suitable for high pulse current operation
- Good spectral matching with CMOS cameras
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



APPLICATIONS

- Infrared radiation source for operation with CMOS cameras
- High speed IR data transmission
- Smoke-automatic fire detectors
- IR Flash

PRODUCT SUMMARY

| COMPONENT | I_e (mW/sr) | φ (deg) | λ_p (nm) | t_r (ns) |
|-----------|---------------|-----------------|------------------|------------|
| VSLY5850 | 600 | ± 3 | 850 | 10 |

Note

- Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM |
|---------------|-----------|------------------------------|-------------------|
| VSLY5850 | Bulk | MOQ: 4000 pcs, 4000 pcs/bulk | T-1 $\frac{3}{4}$ |

Note

- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25^\circ\text{C}$, unless otherwise specified)

| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT |
|-------------------------------------|---|------------|---------------|------------------|
| Reverse voltage | | V_R | 5 | V |
| Forward current | | I_F | 100 | mA |
| Peak forward current | $t_p/T = 0.5$, $t_p = 100 \mu\text{s}$ | I_{FM} | 200 | mA |
| Surge forward current | $t_p = 100 \mu\text{s}$ | I_{FSM} | 1 | A |
| Power dissipation | | P_V | 190 | mW |
| Junction temperature | | T_j | 100 | $^\circ\text{C}$ |
| Operating temperature range | | T_{amb} | - 40 to + 85 | $^\circ\text{C}$ |
| Storage temperature range | | T_{stg} | - 40 to + 100 | $^\circ\text{C}$ |
| Soldering temperature | $t \leq 5$ s, 2 mm from case | T_{sd} | 260 | $^\circ\text{C}$ |
| Thermal resistance junction/ambient | J-STD-051, leads 7 mm, soldered on PCB | R_{thJA} | 230 | K/W |

** Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

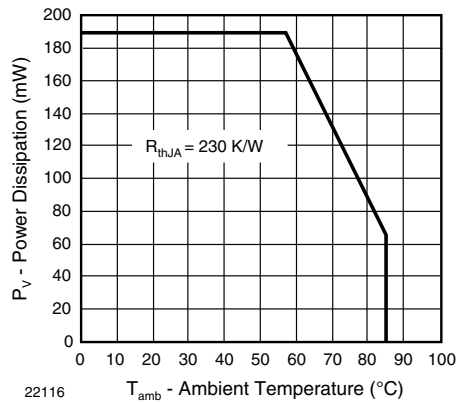


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

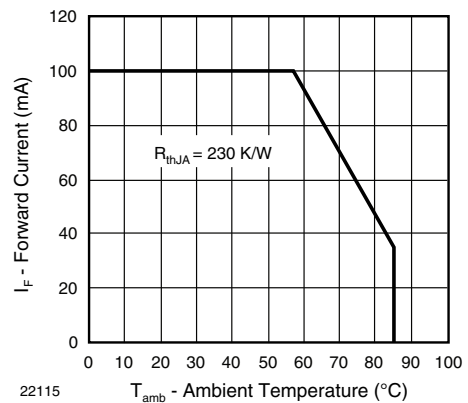


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified) | | | | | | |
|--|---|-----------------------------|------------------------------------|--------|------|-------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Forward voltage | I _F = 100 mA, t _p = 20 ms | V _F | | 1.65 | 1.9 | V |
| | I _F = 1 A, t _p = 100 μs | V _F | | 2.9 | | V |
| Temperature coefficient of V _F | I _F = 1 mA | TK _{V_F} | | - 1.45 | | mV/K |
| | I _F = 10 mA | TK _{V_F} | | - 1.25 | | mV/K |
| Reverse current | | I _R | not designed for reverse operation | | | μA |
| Junction capacitance | V _R = 0 V, f = 1 MHz, E = 0 | C _j | | 125 | | pF |
| Radiant intensity | I _F = 100 mA, t _p = 20 ms | I _e | 300 | 600 | 900 | mW/sr |
| | I _F = 1 A, t _p = 100 μs | I _e | | 5100 | | mW/sr |
| Radiant power | I _F = 100 mA, t _p = 20 ms | φ _e | | 55 | | mW |
| Temperature coefficient of φ _e | I _F = 100 mA | TKφ _e | | - 0.35 | | %/K |
| Angle of half intensity | | φ | | ± 3 | | deg |
| Peak wavelength | I _F = 100 mA | λ _p | 840 | 850 | 870 | nm |
| Spectral bandwidth | I _F = 100 mA | Δλ | | 30 | | nm |
| Temperature coefficient of λ _p | I _F = 100 mA | TKλ _p | | 0.25 | | nm/K |
| Rise time | I _F = 100 mA | t _r | | 10 | | ns |
| Fall time | I _F = 100 mA | t _f | | 10 | | ns |

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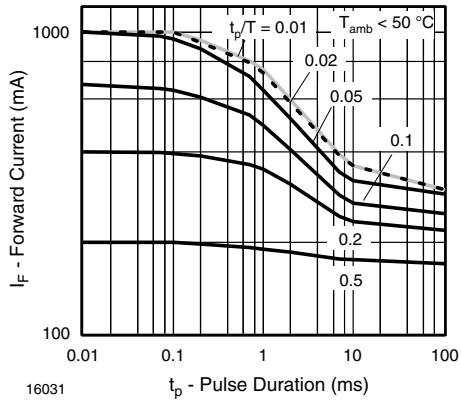
BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)


Fig. 3 - Pulse Forward Current vs. Pulse Duration

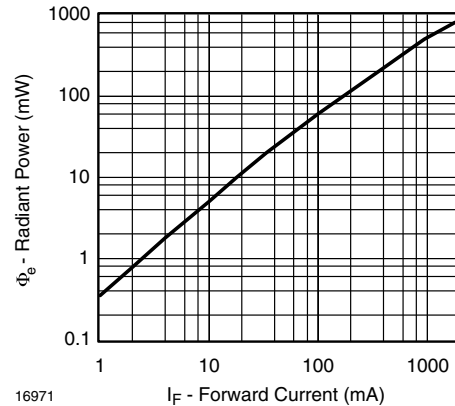


Fig. 6 - Radiant Power vs. Forward Current

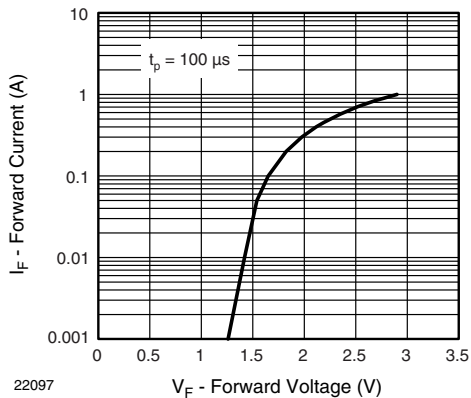


Fig. 4 - Forward Current vs. Forward Voltage

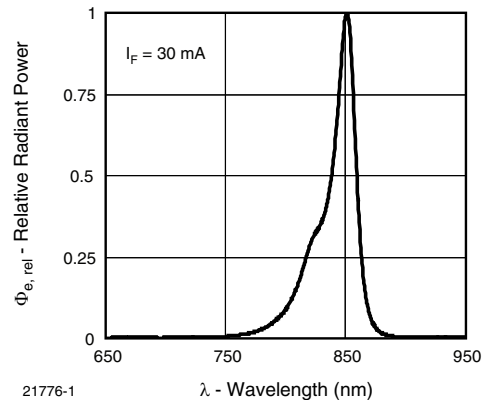


Fig. 7 - Relative Radiant Power vs. Wavelength

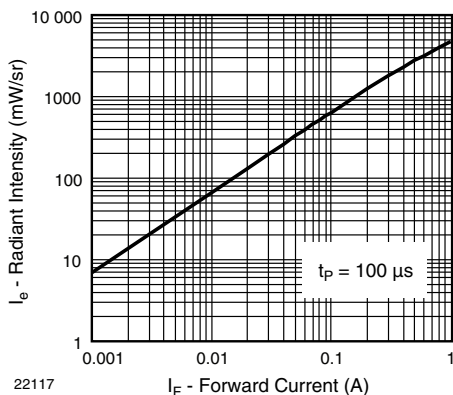


Fig. 5 - Radiant Intensity vs. Forward Current

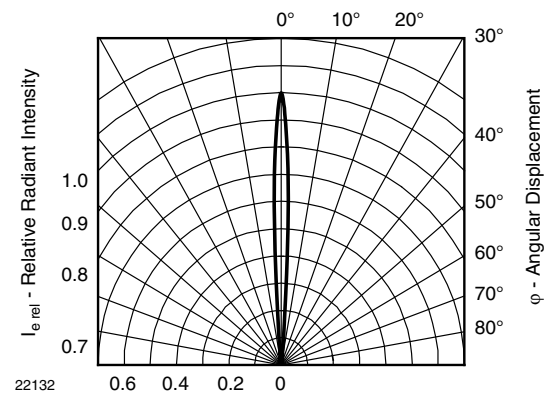
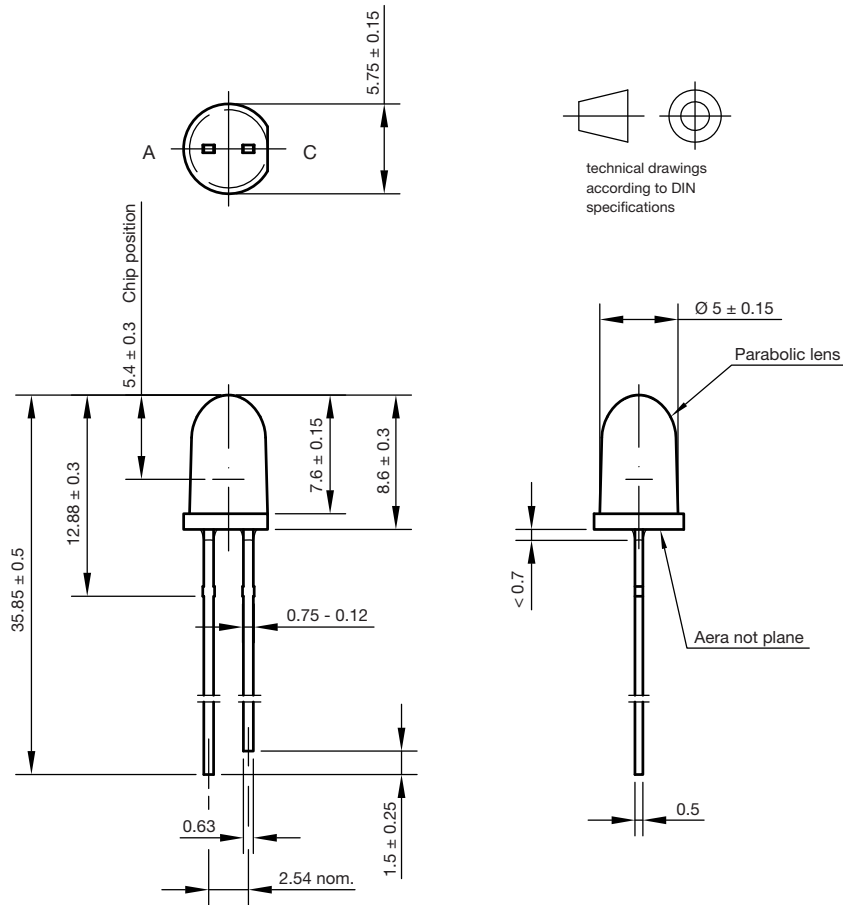


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



technical drawings
according to DIN
specifications

Drawing-No.: 6.544-5385.01-4
Issue: 2; 08.03.10
20531

Not indicated tolerances ± 0.1



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